

Octal 3-State Inverting Buffer / Line Driver / Line Receiver in bare die form

Description

The 74AC240 is produced on a 1.5µm 5V CMOS process combining high speed LSTTL performance with CMOS low power. The device can be used as two 4-bit buffers or one 8-bit buffer & features inverting inputs with two output enables, each controlling four of the 3-state outputs. The device is designed to improve performance & density in clock drivers, 3-state memory address drivers & bus orientated transmitters and receivers. Inputs accept standard CMOS outputs or LSTTL outputs using pull-up resistors. Inputs are also equipped with protection circuits against static discharge and transient excess voltage.

Ordering Information

The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection

For High Reliability versions of this product places s

54AC240

Supply Formats

- Defact Die in Waffle Pack (100 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Features:

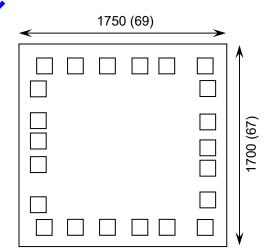
- Outputs Sink/Source 24mA
- Low Input Current: 1µA
- Outputs directly interface Chief, NMOS and TTL

Rev 1.1

30/11/21

- Operating Voltage Range: 2% to 6V
- CMOS High Noise Immunity
- Function compatible with 74LS240
- Lower power alternative to Bipolar or BiCMOS logic.

Die Dimensions in µm (mils)



Mechanical Specification

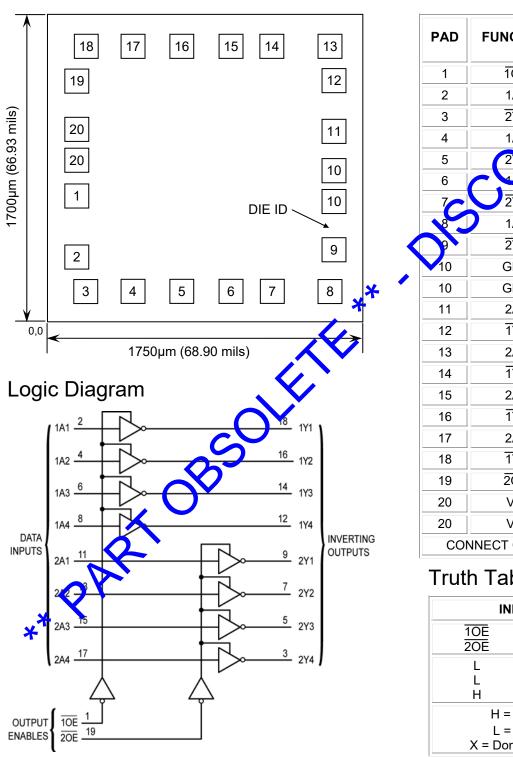
Die Size (Unsawn)	1750 x 1700 69 x 67	µm mils	
Minimum Bond Pad Size	130 x 130 5.12 x 5.12	µm mils	
Die Thickness	350 (±20) μr 13.78 (±0.79) mi		
Top Metal Composition	Al 1%Si 1.1µm		
Back Metal Composition	N/A – Bare Si		





Pad Layout and Functions

Rev 1.1 30/11/21



PAD FU	FUNCTION	COORDINATES (mm)				
FAD		X	Y			
1	10E	0.100	0.630			
2	1A1	0.100	0.290			
3	<u>2Y4</u>	0.150	0.100			
4	1/2	0.410	0.100			
5	273	0.680	0.100			
6	143	0.950	0.100			
7	<u>2Y2</u>	1.180	0.100			
8	1A4	1.500	0.100			
9	2Y1	1.520	0.330			
10	GND	1.520	0.600			
10	GND	1.520	0.770			
11	2A1	1.520	0.990			
12	<u>1Y4</u>	1.520	1.270			
13	2A2	1.500	1.460			
14	1Y3	1.180	1.460			
15	2A3	0.950	1.460			
16	1Y2	0.680	1.460			
17	2A4	0.410	1.460			
18	1Y1	0.150	1.460			
19	20E	0.100	1.270			
20	V _{cc}	0.100	1.000			
20	V _{cc}	0.100	0.830			
CONNECT CHIP BACK TO V _{CC} OR FLOAT						

Truth Table

INP	OUTPUTS					
10E 20E	1A, 2A	1Y, 2Y				
L	L	Н				
L	Н	L				
H	X	Z				
H = High level (steady state) L = Low level (steady state) X = Don't care, Z = High impedance						





Pad Descriptions

ADDRESS INPUTS

1A1, 1A2, 1A3, 1A4, 2A1, 2A2, 2A3, 2A4 (Pads 2, 4, 6, 8, 11, 13, 15, 17) Data input pins. Data on these pins appear in inverted form on the corresponding Y outputs, when the outputs are the t

CONTROL INPUTS

10E, 20E (Pads 1, 19)

Output enables (active–low). When a low level is applied to these pins, the outputs are enabled and the devices function as inverters. When a high level is applied, the outputs assume the high impedance state.

OUTPUTS

1Y1, 1Y2, 1Y3, 1Y4, 2Y1, 2Y2, 2Y3, 2Y4

(Pads 18, 16, 14, 12, 9, 7, 5, 3)

Device outputs. Depending upon the state of the output enable pins, these outputs are either inverting outputs or high-impedance outputs.

Absolute Maximum Ratings¹

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V _{cc}	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V _{IN}	-0.5 to V _{CC} +0.5	V
DC Output Voltage (Referenced to GND)	V _{OUT}	-0.5 to V _{CC} +0.5	V
DC Input Current, per pin	I _{IN}	±20	mA
DC Output Current, per pin	I _{OUT}	±50	mA
DC V _{cc} or GND Current, per pin	I _{CC}	±50	mA
Power Dissipation in Still Air ²	PD	750	mW
Storage Temperature Range	T _{STG}	-65 to 150	°C

1. Operation above the absolute maximum ating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in prestic D¹² package, results in die form are dependent on die attach and assembly method.

Recommended Operating Conditions³ (Voltages referenced to GND)

PARAMETER	SYMBOL	MIN	MAX	UNITS	
DC Supply Voltage	V _{CC}	2	6	V	
DC Input or Output Voltage	V _{IN} ,V _{OUT}	0	V _{CC}	V	
Operating Temporature Rai	TJ	-40	+85	°C	
Output Current - High	I _{OH}	-	-24	mA	
Output Current – Low	I _{OL}	-	24	mA	
Input Rise and Fall Time (V _{IN} from 30% to 70%)	V _{CC} = 3.0V		0	150	
	$V_{CC} = 4.5V$	t _r , t _f	0	40	ns/V
	$V_{\rm CC} = 5.5 V$		0	24	

3. This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND $\leq (V_{IN} \text{ or } V_{OUT}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Rev 1.1 30/11/21



Rev 1.1 30/11/21

PARAMETER	SYMBOL	V _{cc}	CONDITIONS	LIMITS			
				25°C	85°C	FULL RANGE ⁴	
		3.0V	$V_{OUT} = 0.1V \text{ or}$ $V_{CC} - 0.1V$	2.1	2.1	2.1	V
Vinimum High-Level Input Voltage	V _{IH}	4.5V		3.15	3.15	3.15	
1 5		5.5V	Ι _{ουτ} ≤ 20μΑ	3.85	3.85	3.85	
/laximum Low-Level		3.0V	$V_{OUT} = 0.1 V \text{ or}$	0.9	0.9	7.9	V
Input Voltage	V _{IL}	4.5V	V _{CC} -0.1V I _{OUT} ≤ 20μA	1.35	1.35	1.35	
1 0		5.5V	$ I_{OUT} \leq 20\mu A$	1.65	1.65	1.65	
		3.0V		2.9	2.9	2.9	
		4.5V	Ι _{ΟUT} = -50μΑ	4.4	44	4.4	
		5.5V		5.4	54	5.4	
/inimum High-Level		3.0V	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{OH} = -12 \text{ mA}$	2.55	2.46	2.46	V
Output Voltage	V _{OH}	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{OH} = -24 \text{mA}^5$	380	3.76	3.76	
		5.5V	$V_{IN} = V_{IL} \text{ or } V_{A}$ $I_{OH} = -24n^{45}$	4.86	4.76	4.76	
		5.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{OH} = \sqrt{5}mA^6$	-	3.85	3.85	
	4.5V 5.5W V _{OL} .0V 5.5V	3.0V		0.1	0.1	0.1	
		4.5V	ί _{ουτ} = 50μΑ	0.1	0.1	0.1	
		5.5		0.1	0.1	0.1	
laximum Low-Level		.0V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 12 \text{mA}$	0.36	0.44	0.5	
Output Voltage		2 .5V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 24 \text{mA}^5$	0.36	0.44	0.5	V
		5.5V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 24 \text{mA}^5$	0.36	0.44	0.5	
		5.5V	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} 75mA^{6}$	-	1.65	1.65	
Maximum Input Leakage Cutrent	I _{IN}	5.5V	$V_{IN} = V_{CC}$ or GND	±0.1	±1.0	±1.0	μA
Maximum o-State Leakage Current	I _{oz}	5.5V	$V_{OUT}=V_{CC} \text{ or } GND$ $V_{IN}=V_{IL} \text{ or } V_{IH}$	±0.5	±2.5	±2.5	μA
Minimum Dynamic	I _{OLD}	5.5V	V _{OLD} = 1.65V Max	-	75	75	
Output Current ⁷	I _{OHD}	5.5V	V _{OHD} = 3.85V Min	-	-75	-75	mA
Maximum Quiescent Supply Current	I _{CC}	5.5V	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\mu A$	8	80	80	μA

4. $-40^{\circ}C \le T_{J} \le +85^{\circ}C$ **5.** All outputs loaded; thresholds on input associated with output under test. **6.** Test time 1sec max, measurement made by forcing indicated current and measuring voltage to minimize power dissipation. Test verifies a minimum 75 Ω transmission-line drive capability at 125°C **7.** Maximum test duration 2ms, one output loaded at a time





Rev 1.1 30/11/21

AC Electrical Characteristics ⁸ (V _{cc} 3.3V ±0.3V, V _{cc} 5V ±0.3V)						30/11/2	
PARAMETER	SYMBOL	V _{cc}		LIMITS			
		•		25°C	85°C	FULL RANGE ⁴	
	t _{PLH,}	3.3V	C _L = 50pF, Input	8.0	9.0	9.0	ns
Maximum Propagation Delay	PLH,	5.0V	$t_r = t_f = 3ns$	6.5	7.0	7.0	
Input A to Output Y (Figure 1,3)	t _{PHL}	3.3V	C _L = 50pF, Input	8.0	8.5	8.3	ns
	PHL	5.0V	$t_r = t_f = 3ns$	6.0	6.5	6.5	
	t _{PZH,}	3.3V	C _L = 50pF, Input	10.5	1.0	11.0	ns
Output Enable Time OE to 1Y or 2Y		5.0V	$t_r = t_f = 3ns$	7.0	8.0	8.0	. 115
(Figure 2,4)	t _{PZL}	3.3V	C _L = 50pF, Input	10.0	11.0	11.0	ns
		5.0V	$t_r = t_f = 3ns$	8.0	8.5	8.5	113
Output Enable Time OE to 1Y or 2Y (Figure 2,4)	t _{PHZ}	3.3V	$C_L = 50 pF,$	10	10.5	10.5	ns
		5.0V	Input¥ t _r = t _f ¥3ns	9.0	9.5	9.5	113
	t _{PLZ}	3.3V	L≓ 50pF,	10.5	11.5	11.5	ns
		5.0V	$t = t_f = 3ns$	9.0	9.5	9.5	113
Maximum Input Capacitance	C _{IN}		-	4.5	4.5	4.5	pF
Power Dissipation			$T_J = 25^{\circ}C,$	TYPICAL			
Capacitance ⁹		\mathbf{r}	$V_{CC} = 5.0V$		4	5	pF

8. Not production tested in die form, ch trackeized by chip design 9. Used to determine the no-load dracate over consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

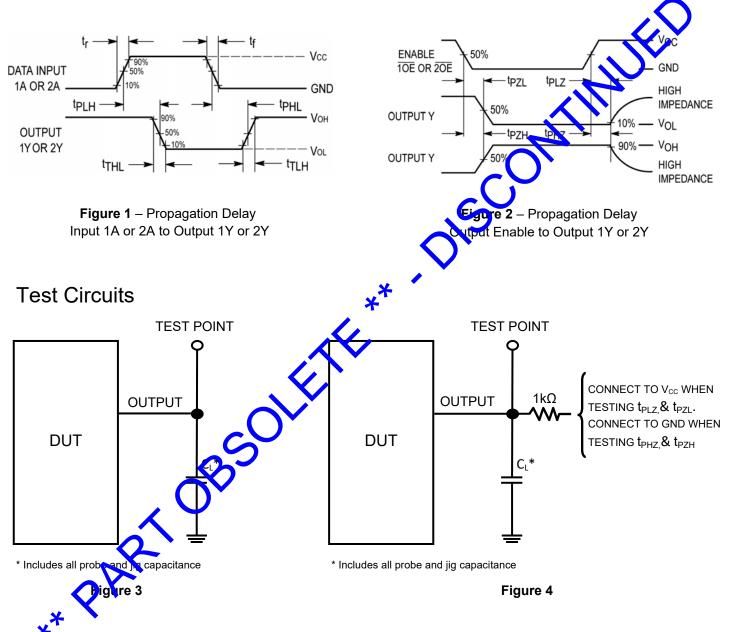
** PARI





Rev 1.1 30/11/21

Switching Waveforms



DISCLAIMER: The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Silicon Supplies Ltd hereby disclaims any and all warranties and liabilities of any kind.

LIFE SUPPORT POLICY: Silicon Supplies Ltd components may be used in life support devices or systems only with the express written approval of Silicon Supplies Ltd, if a failure of such components can reasonably be expected to cause the failure of that life support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

